

N-Channel Enhancement Mode MOSFET

TDM3432

DESCRIPTION

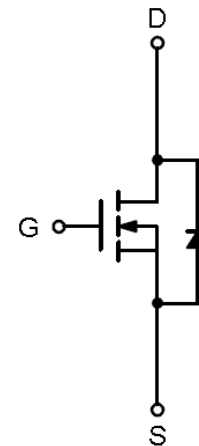
The TDM3432 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

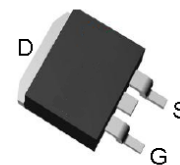
- RDS(ON) < 4.1mΩ @ VGS=4.5V
RDS(ON) < 3.1mΩ @ VGS=10V
- High Power and current handling capability
- Lead free product is available
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



N-Channel MOSFET



Top View of TO-263-3

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	40	V
Gate-Source Voltage	VGS	±20	V
Drain Current @ Continuous	ID (TA=25°C)	25	A
	ID (TA=70°C)	20	A
Drain Current @ Current-Pulsed (Note 1)	IDM (Tc=25°C)	300	A
Drain Current @ Continuous	ID (Tc=25°C)	100	A
	ID (Tc=100°C)	78	A
Maximum Power Dissipation (TA=25°C)	Pd	2.7	W
Maximum Operating Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance,Junction-to-Ambient (Note 1)	RθJA	50	°C/W
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TDM3432
ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

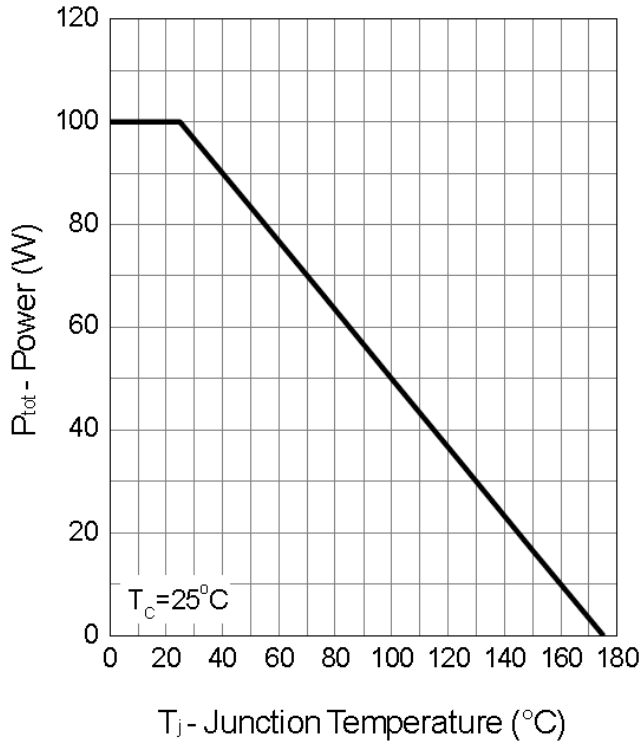
Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=32V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.4	1.7	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=20A$		3.1	4.1	m Ω
		$V_{GS}=10V, I_D=25A$		2.4	3.1	m Ω
DYNAMIC CHARACTERISTICS (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V, F=1.0MHz$		2650		PF
Output Capacitance	C_{oss}			750		PF
Reverse Transfer Capacitance	C_{rss}			88		PF
SWITCHING CHARACTERISTICS (Note 3)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=20V, R_L=20\Omega, V_{GEN}=10V, R_G=6\Omega, I_D=1A$		17		nS
Turn-on Rise Time	t_r			11.5		nS
Turn-Off Delay Time	$t_{d(off)}$			36		nS
Turn-Off Fall Time	t_f			31		nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=25A, V_{GS}=4.5V$		17		nC
Gate-Source Charge	Q_{gs}			7		nC
Gate-Drain Charge	Q_{gd}			5.3		nC
Body Diode Reverse Recovery Time	T_{rr}	$I_F=5A, di/dt=100A/\mu s$		38		nS
Body Diode Reverse Recovery Charge	Q_{rr}			35		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 2)	V_{SD}	$V_{GS}=0V, I_S=20A$		0.8	1.1	V

NOTES:

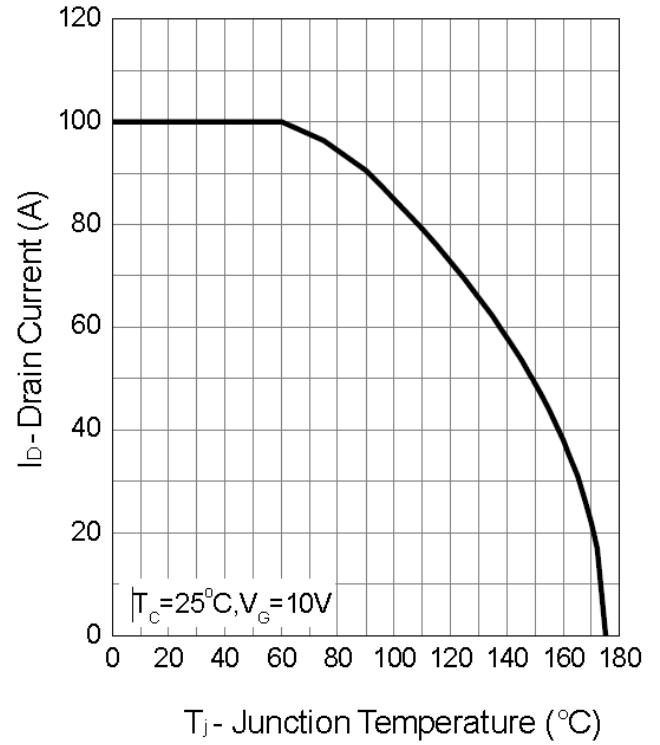
1. Pulse width limited by max. junction temperature.
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
3. Guaranteed by design, not subject to production testing

Typical Operating Characteristics

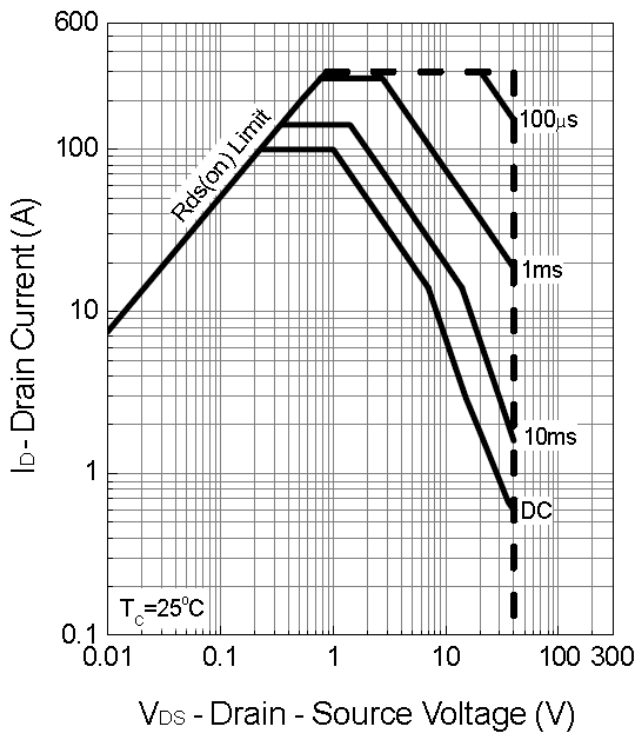
Power Dissipation



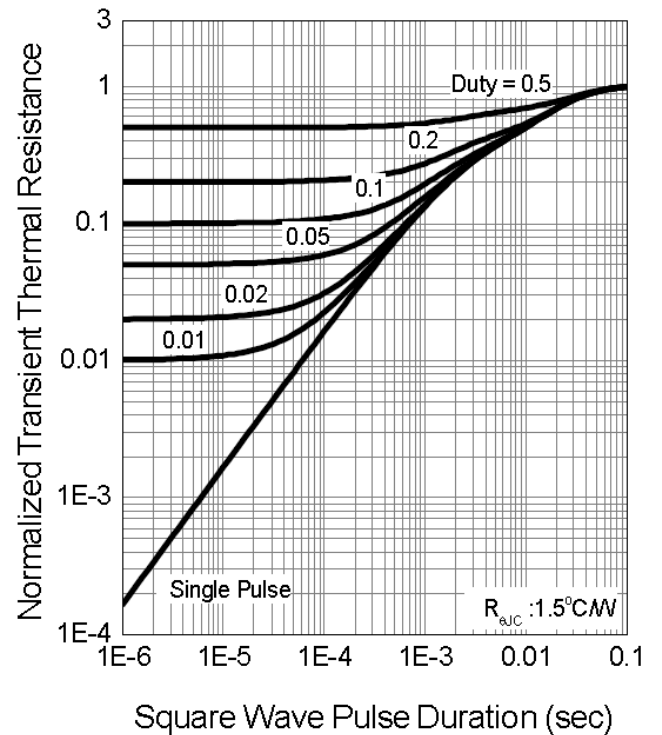
Drain Current



Safe Operation Area

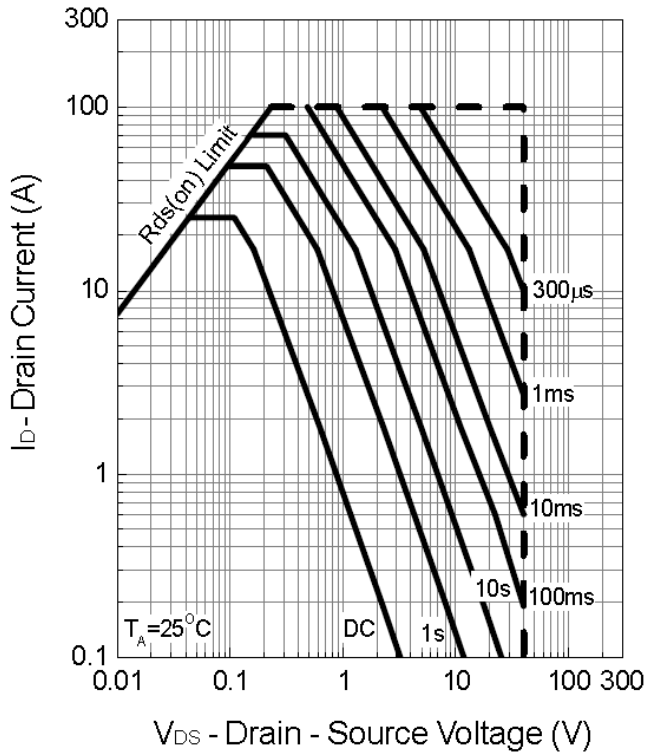


Thermal Transient Impedance

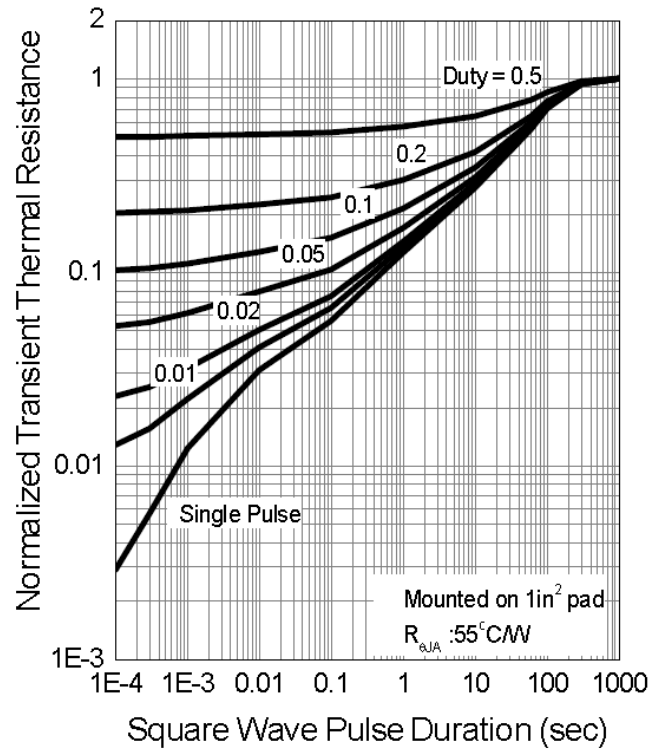


Typical Operating Characteristics(Cont.)

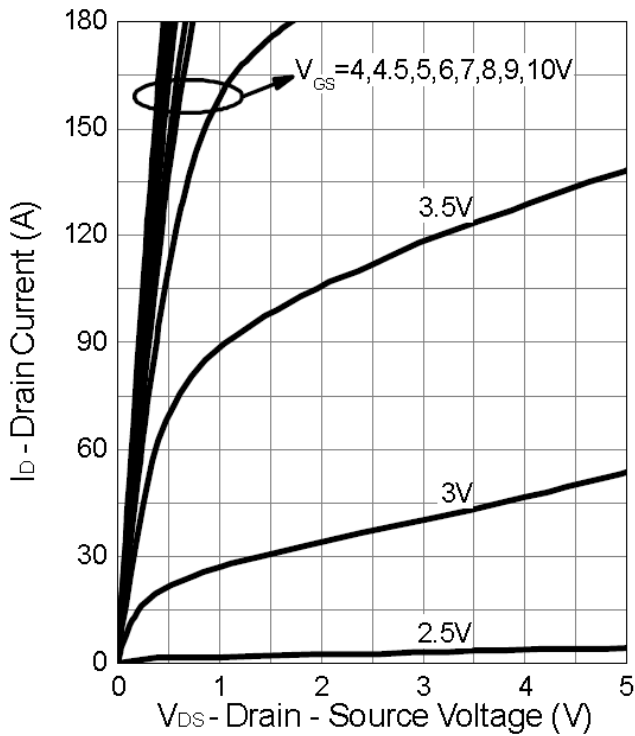
Safe Operation Area



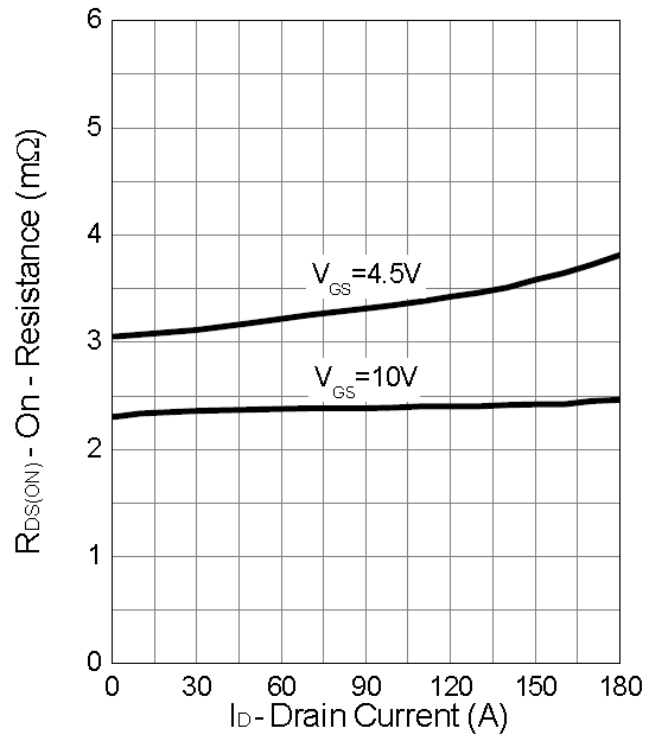
Thermal Transient Impedance



Output Characteristics

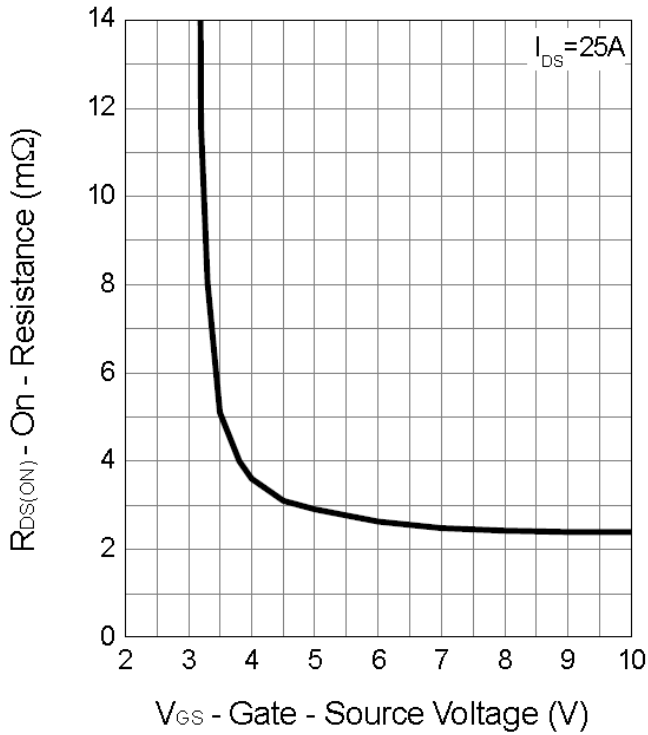


Drain-Source On Resistance

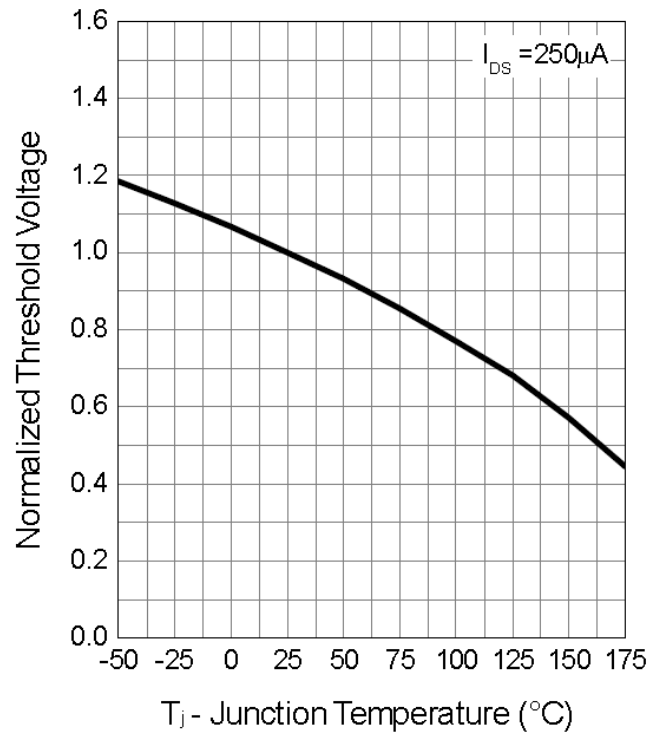


Typical Operating Characteristics (Cont.)

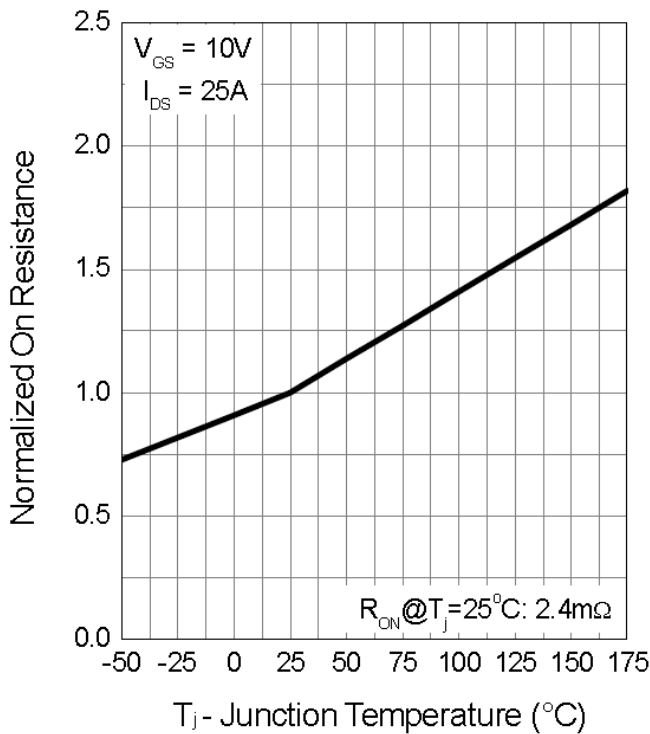
Gate-Source On Resistance



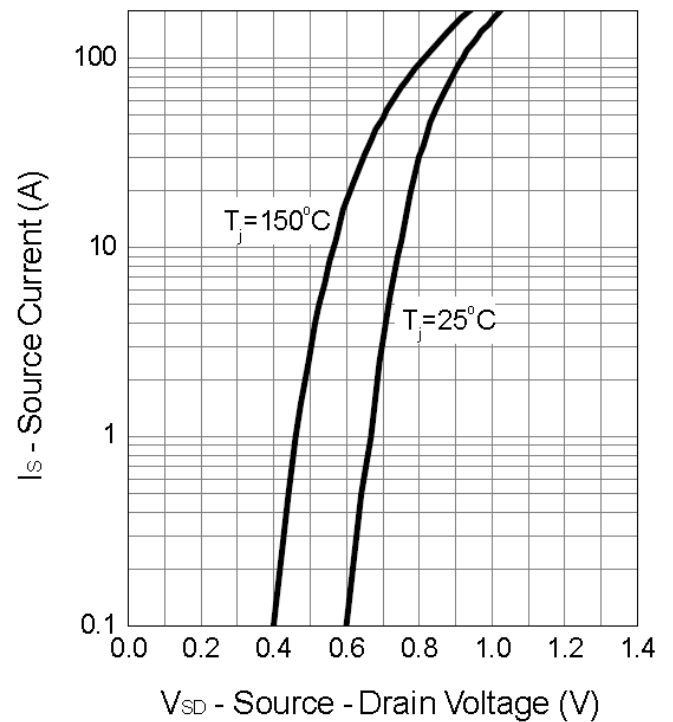
Gate Threshold Voltage



Drain-Source On Resistance

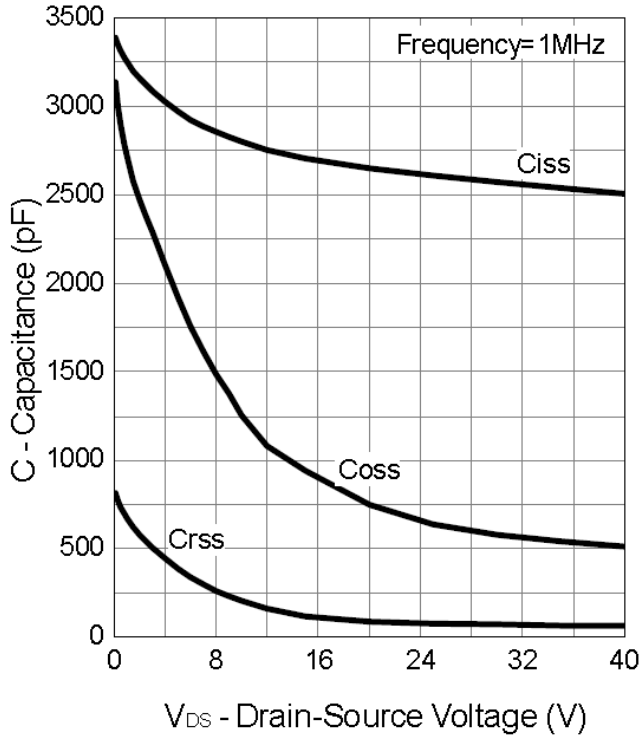


Source-Drain Diode Forward

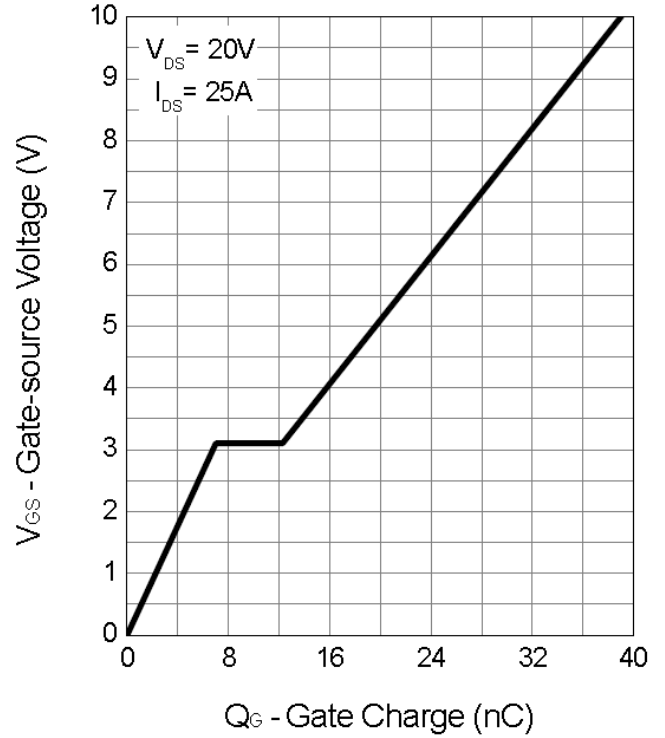


Typical Operating Characteristics (Cont.)

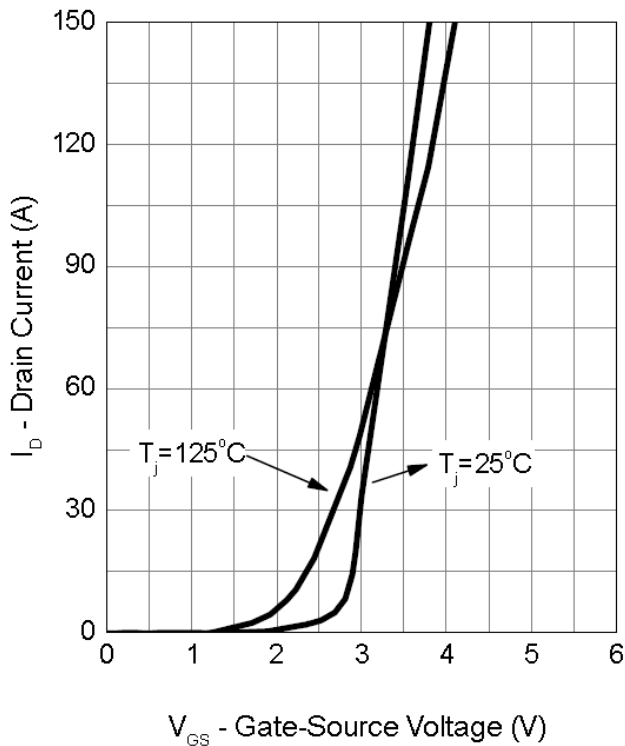
Capacitance



Gate Charge

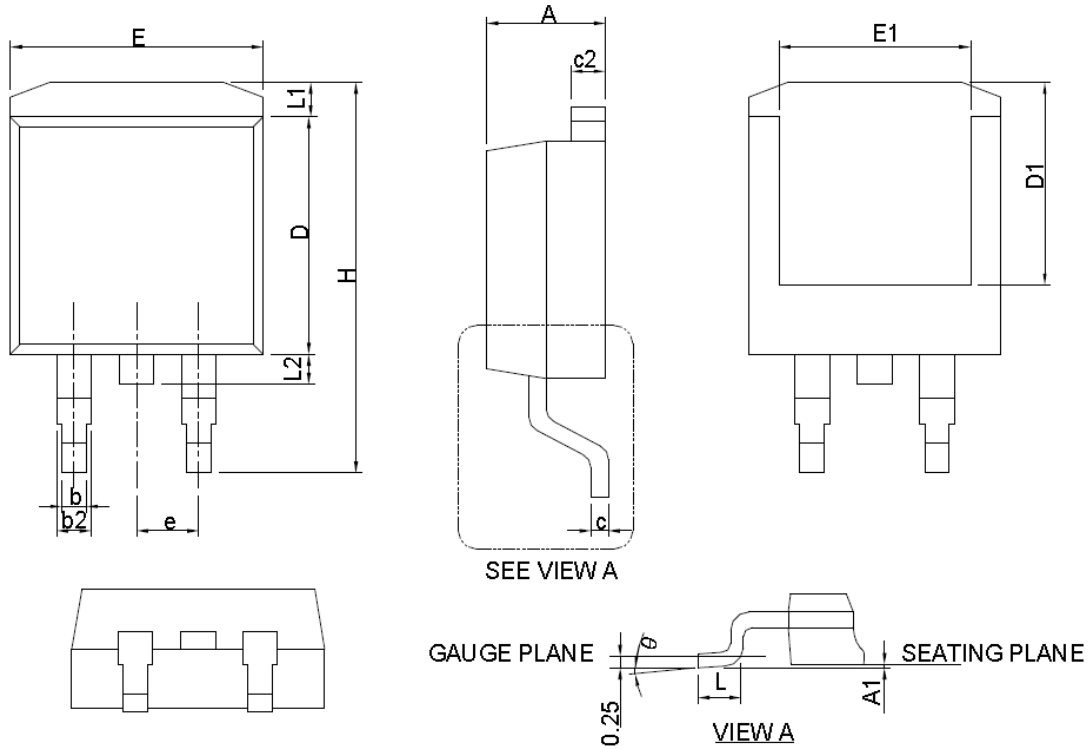


Transfer Characteristics



Package Information

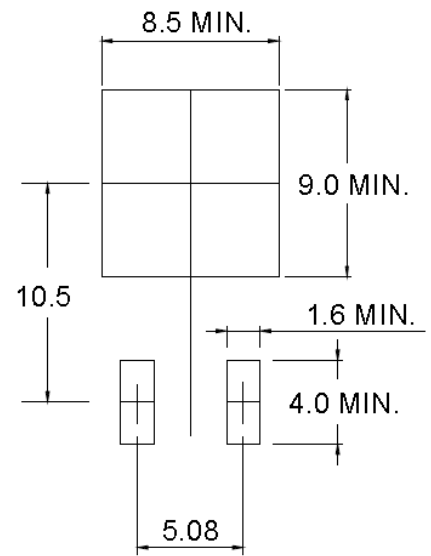
TO263-3 Package



SYMBOL	TO-263-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b2	1.14	1.78	0.045	0.070
c	0.38	0.74	0.015	0.029
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380
D1	6.00	9.00	0.236	0.354
E	9.65	11.43	0.380	0.450
E1	6.22	9.00	0.245	0.354
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.68	-	0.066
L2	-	1.78	-	0.070
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-263 AB.

RECOMMENDED LAND PATTERN



UNIT: mm

Design Notes